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(54) Title: METHOD FOR FABRICATING SEMICONDUCTOR COMPONENTS USING MASKLESS BACK SIDE ALIGNMENT TO CONDUCTIVE VIAS

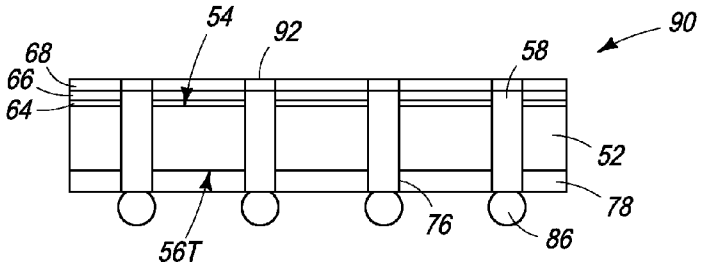


FIG. 6C

(57) Abstract: A method for fabricating semiconductor components (90) includes the steps of: providing a semiconductor substrate (52) having a circuit side (54), a back side (56) and conductive vias (58); removing portions of the substrate (52) from the back side (56) to expose terminal portions (76) of the conductive vias (58); depositing a polymer layer (78) on the back side (56) encapsulating the terminal portions (76); and then planarizing the polymer layer (78) and ends of the terminal portions (76) to form self aligned conductors embedded in the polymer layer (78). Additional back side elements, such as terminal contacts (86) and back side redistribution conductors (88), can also be formed in electrical contact with the conductive vias (58). A semiconductor component (90) includes the semiconductor substrate (52), the conductive vias (58), and the back side conductors embedded in the polymer layer (78). A stacked semiconductor component (96) includes a plurality of components (90-1, 90-2, 90-3) having aligned conductive vias (58) in electrical communication with one another.